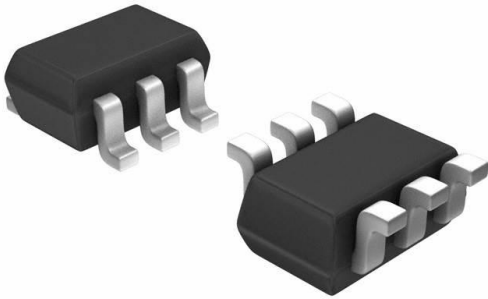


# 2N7002DW Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	2N7002DW-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	2N7002DW
Description	MOSFET 2N-CH 60V 0.115A SC88
Detailed Description	Mosfet Array 60V 115mA 200mW Surface Mount SC-88 (SC-70-6)



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

2N7002DW

Series:

-

Technology:

MOSFET (Metal Oxide)

FET Feature:

Logic Level Gate

Current - Continuous Drain (Id) @ 25°C:

115mA

Vgs(th) (Max) @ Id:

2V @ 250µA

Input Capacitance (Ciss) (Max) @ Vds:

50pF @ 25V

Operating Temperature:

-55°C ~ 150°C (Tj)

Package / Case:

6-TSSOP, SC-88, SOT-363

Base Product Number:

2N7002

Manufacturer:

onsemi

Product Status:

Active

Configuration:

2 N-Channel (Dual)

Drain to Source Voltage (Vdss):

60V

Rds On (Max) @ Id, Vgs:

7.50hm @ 50mA, 5V

Gate Charge (Qg) (Max) @ Vgs:

-

Power - Max:

200mW

Mounting Type:

Surface Mount

Supplier Device Package:

SC-88 (SC-70-6)

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

# Field Effect Transistor - N-Channel, Enhancement Mode

## 2N7002DW

### Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

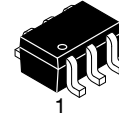
Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \leq 1.0\text{ M}\Omega$ )	60	V
$V_{GSS}$	Gate-Source Voltage	Continuous	$\pm 20$
		Pulsed	$\pm 40$
$I_D$	Drain Current	Continuous	115
		Continuous at 100 °C	73
		Pulsed	800
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

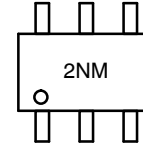
Symbol	Parameter	Ratings	Unit
$P_D$	Total Device Dissipation	200	mW
	Derate Above $T_A = 25\text{ }^\circ\text{C}$	1.6	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	415	$^\circ\text{C}/\text{W}$

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.



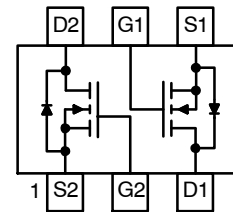
SC-88/SC70-6/SOT-363  
CASE 419B-02

### MARKING DIAGRAM



2N = Specific Device Code  
M = Assembly Operation Month

### PIN CONNECTIONS



### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

## 2N7002DW

## ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping <sup>†</sup>
2N7002DW	2N	SC70-6 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

ELECTRICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

## OFF CHARACTERISTICS (Note 2)

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	60	78	–	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	–	0.001	1.0	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	–	7	500	
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	–	0.2	$\pm 10$	nA

## ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.00	1.76	2.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 5\text{ V}, I_D = 0.05\text{ A}$	–	1.6	7.5	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$	–	–	2.0	
		$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}, T_J = 125\text{ }^\circ\text{C}$	–	2.53	13.5	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 7.5\text{ V}$	0.50	1.43	–	A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 0.2\text{ A}$	80.0	356.5	–	mS

## DYNAMIC CHARACTERISTICS

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	–	37.8	50	pF
$C_{oss}$	Output Capacitance		–	12.4	25	pF
$C_{rss}$	Reverse Transfer Capacitance		–	6.5	7	pF

## SWITCHING CHARACTERISTICS (Note 2)

$t_{D(ON)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 0.2\text{ A}, V_{GEN} = 10\text{ V}, R_L = 150\text{ }\Omega, R_{GEN} = 25\text{ }\Omega$	–	5.85	20	ns
$t_{D(OFF)}$	Turn-Off Delay Time		–	12.5	20	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Short duration test pulse used to minimize self-heating effect.

## TYPICAL PERFORMANCE CHARACTERISTICS

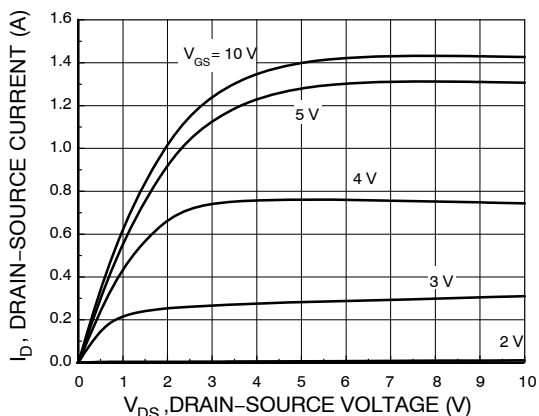


Figure 1. On-Region Characteristics

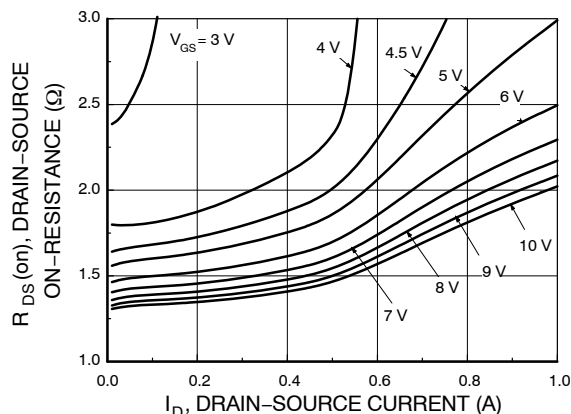
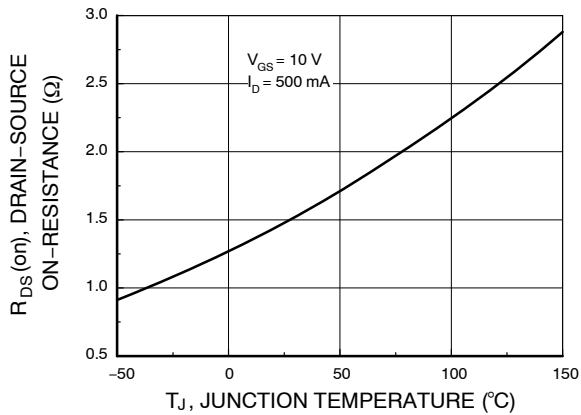


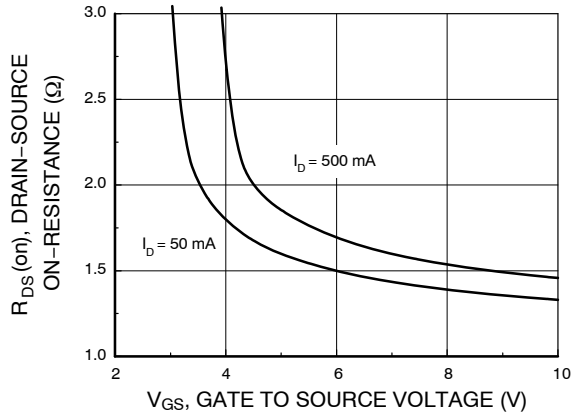
Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

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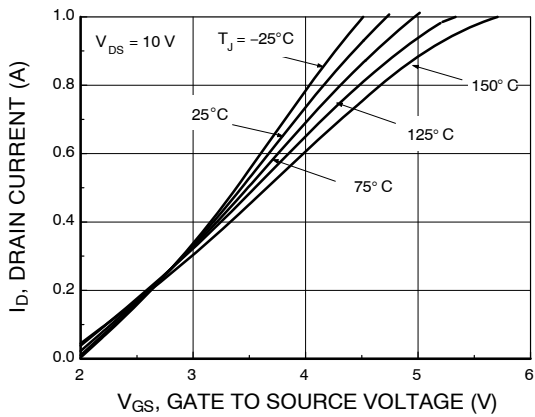
## TYPICAL PERFORMANCE CHARACTERISTICS (continued)



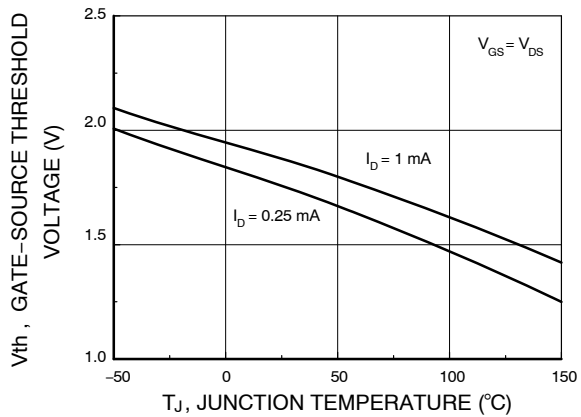
**Figure 3. On-Resistance Variation with Temperature**



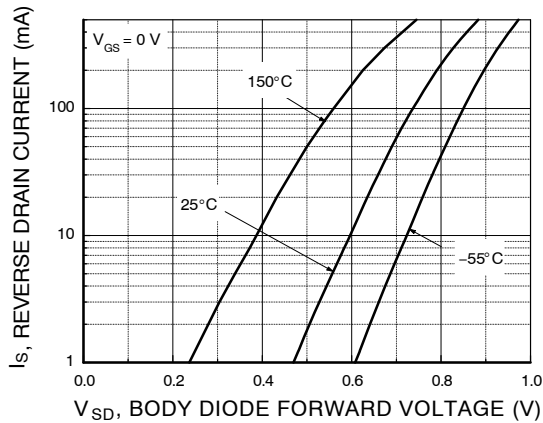
**Figure 4. On-Resistance Variation with Gate-Source Voltage**



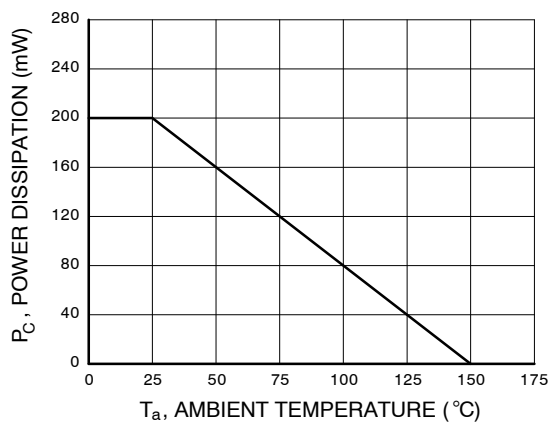
**Figure 5. Transfer Characteristics**



**Figure 6. Gate Threshold Variation with Temperature**



**Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature**



**Figure 8. Power Derating**

# 2N7002DW

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

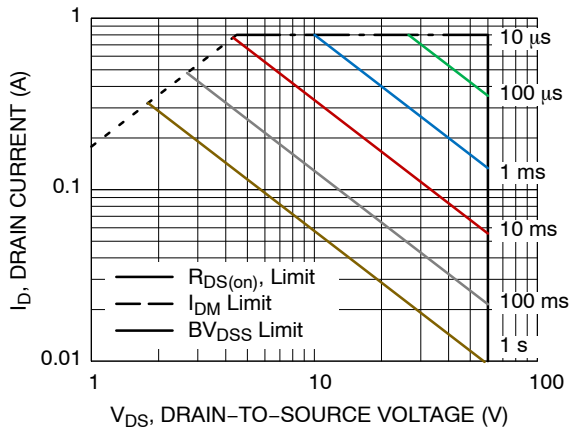


Figure 9. SOA

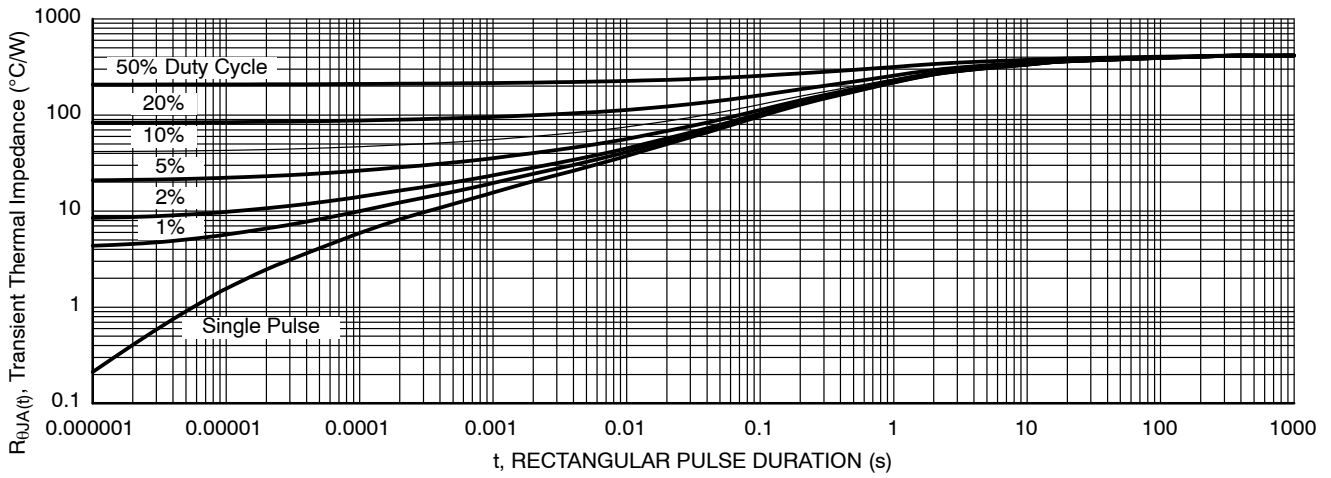


Figure 10. Transient Thermal Impedance vs Pulse Time



**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**

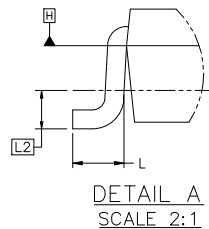
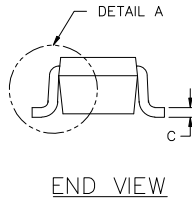
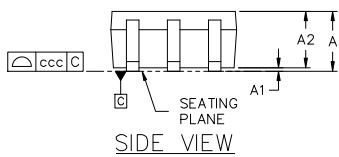
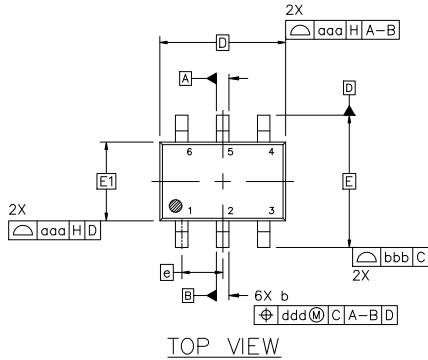


**SC-88 2.00x1.25x0.90, 0.65P**  
CASE 419B-02  
ISSUE Z

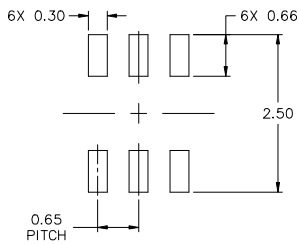
DATE 18 APR 2024

NOTES:

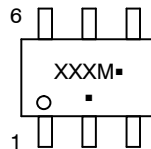
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**STYLES ON PAGE 2**

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**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

<b>STYLE 1:</b> PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	<b>STYLE 2:</b> CANCELLED	<b>STYLE 3:</b> CANCELLED	<b>STYLE 4:</b> PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	<b>STYLE 5:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 6:</b> PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
<b>STYLE 7:</b> PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	<b>STYLE 8:</b> CANCELLED	<b>STYLE 9:</b> PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	<b>STYLE 10:</b> PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	<b>STYLE 11:</b> PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	<b>STYLE 12:</b> PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
<b>STYLE 13:</b> PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 14:</b> PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	<b>STYLE 16:</b> PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	<b>STYLE 17:</b> PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	<b>STYLE 18:</b> PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
<b>STYLE 19:</b> PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	<b>STYLE 20:</b> PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	<b>STYLE 21:</b> PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	<b>STYLE 22:</b> PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	<b>STYLE 23:</b> PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	<b>STYLE 24:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
<b>STYLE 25:</b> PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	<b>STYLE 26:</b> PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	<b>STYLE 27:</b> PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	<b>STYLE 28:</b> PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	<b>STYLE 29:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	<b>STYLE 30:</b> PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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